

### Remarks

Claims 19 has been amended with the details set forth in Attachment I (Version with Markings to Show Changes Made). Claims 20, 22, and 26 have been cancelled.

### The 35 USC 112 Rejection

The rejection of Claim 26 under 35 USC 112, first paragraph, has been rendered moot by cancellation of that claim.

### The 35 USC 103 Rejections

Claims 19-30 are rejected under 35 USC 103(a) as unpatentable over Russo taken in view of Moto and Cotell, and as unpatentable over those references in view of Gartner I or Face or Koga or Menhrotra. None of the applied references teach or suggest all the features of Claim 19, for example, or the structural features of Claims 21, 23, 24, let alone the more specific features of Claims 25 and 27-30. It is noted that the rejection is primarily based on the features of parent Claim 19. Thus, in view of the amendments to the parent Claim 19 and the features of the dependent claims, it is submitted that this ground of rejection has been overcome.

Conclusion

In view of the amendments to the claims, the lack of the applied references to teach the features of the claims, and the cancellation of certain claims, it is submitted that these grounds of rejection have been overcome. Thus, this application is in condition for allowance based on Claims 19, 21, 23-25, and 27-30.

Respectfully submitted,

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Enclosure:  
Attachment I

Attachment I  
S. N. 09/636,134  
Version with Markings to Show Changes Made

In The Claims

Claims 19 amend to read as follows:

19. (Four Times Amended) An apparatus for depositing a material having a work function of approximately 1eV on a substrate by laser ablation using short-wavelength photons, including:
- a deposition chamber,
  - a target containing a material having a work function of approximately 1eV in said chamber,
  - a laser capable of directing photons at or below visible wavelength into said chamber and onto said target,
  - means for rotating said target,
  - means for controlling the composition of the deposit by controlling at least one of the groups consisting of the environment of said deposition chamber, the target composition, and the target temperature.
  - a substrate located in said chamber,
  - means for holding said substrate,
  - means for rotating and tilting said substrate, [and]
  - means for processing the surface of the substrate[.], and
  - means for heating and cooling said substrate.
- Claim 20, cancel.
- Claim 22, cancel.
- Claim 26, cancel.